

IEEE ANDREW S. GROVE AWARD

RECIPIENTS

(Formerly the IEEE Jack A. Morton Award)

- 2024 – TSUNENOBU KIMOTO
Professor, Kyoto University, Kyoto,
Japan “For contributions to silicon carbide
material and power devices.”
- 2023 – H.-S. PHILIP WONG
Willard R. and Inez Kerr Bell
Professor in the School of
Engineering, Stanford University,
Stanford, California, USA “For contributions to novel and advanced
semiconductor device concepts and their
implementation.”
- 2022 – HEIKI RIEL
IBM Fellow, Lead IBM Research
Quantum Europe & Africa, Zurich,
Switzerland “For contributions to materials for
nanoscale electronics and organic light-
emitting devices.”
- 2021 – HIDEAKI AOCHI
Senior Expert, Institute of Memory
Technology Research and
Development, Kioxia Corporation,
Kanagawa, Japan “For pioneering and sustained
contributions to high-density, three-
dimensional flash memory.”
- AND
RYOTA KATSUMATA
Deputy General Manager,
Advanced Memory Development
Center, Kioxia Corporation, Mie,
Japan
- AND
MASARU KITO
Group Manager, Advanced Memory
Development Center, Kioxia
Corporation, Mie, Japan
- 2020 – EVELYN L. HU
Tarr-Coyne Professor
of Applied Physics and Electrical
Engineering, John A. Paulson
School of Engineering and Applied
Sciences, Harvard University,
Cambridge, Massachusetts, USA “For pioneering contributions to
microelectronics fabrication technologies
for nanoscale and photonic devices.”
- 2019 – DIGH HISAMOTO
Chief Senior Scientist,
Hitachi; Ltd., Tokyo, Japan “For pioneering work in the manufacturing
of three-dimensional double-gate MOSFET
devices.”
- 2018 – GURTEJ S. SANDHU
“For contributions to silicon CMOS process
technology that enable DRAM and NAND
memory chip scaling.”

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Senior Fellow, Director, Emerging
Memory Technologies R&D, Micron
Technology Inc., Boise, Idaho, USA

- 2017 – SORIN CRISTOLOVEANU
Director of Research, The French
National Centre for Scientific
Research, Grenoble, France
“For contributions to silicon-on-insulator
technology and thin body devices.”
- 2016 – CARLOS H. DÍAZ
Director, Advanced Logic
Technology Development, Taiwan
Semiconductor Manufacturing Co.,
Hsinchu, Taiwan
“For sustained contributions to and
leadership in foundry advanced CMOS logic
transistor technology.”
- 2015 – MASAYOSHI ESASHI
Professor, Tohoku University,
Sendai, Miyagi, Japan
“For developments in micro-electro-
mechanical systems (MEMS) used in
transportation and industrial electronics.”
- 2014 – SANJAY BANERJEE
Cockrell Regents Chair Professor of
Electrical and Computer Engineering
and Director, Microelectronics
Center, University of Texas,
Austin, Texas, USA
“For contributions to column-IV MOSFETs
and related materials processing.”
- 2013 – SHINICHI TAKAGI
Full Professor, The University of
Tokyo, Tokyo, Japan
“For contributions to the understanding of
transport properties in inversion layers of
high-performance MOSFETs.”
- 2012 – JEAN-PIERRE COLINGE
Head of the Micro-Nano Electronics
Centre, Tyndall National Institute,
University College Cork
Cork, Ireland
“For contributions to silicon-on-insulator
devices and technology.”
- 2011 – JUDY HOYT
Professor, Massachusetts Institute of
Technology,
Cambridge, MA, USA
“For seminal contributions to the
demonstration of Si/Ge lattice mismatch
strain engineering for enhanced carrier
transport properties in MOSFET devices.”

AND

EUGENE A. FITZGERALD
Merton C. Flemings SMA Professor of
Materials Engineering,
Massachusetts Institute of
Technology,
Cambridge, MA, USA

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|---|--|
| 2010 – BIJAN DAVARI
IBM Fellow, Vice President
IBM Corporation
Yorktown Heights, NY, USA | “For contributions to high performance deep-submicron CMOS technology.” |
| 2009 – ERIC FOSSUM
Chairman & CEO, Siimpel Corporation,
Arcadia, CA, USA | “For significant contributions to the invention, development and commercialization of CMOS image sensors.” |
| 2008 – STEFAN LAI
Retired Vice President, Technology & Manufacturing Group, Intel Corporation,
Santa Clara, CA, USA | “For contributions in developing Flash memory into a main stream non-volatile memory and the development of multiple generations of Flash memory technologies” |
| 2007 – JAMES D. PLUMMER
Dean of Engineering
Stanford University,
Stanford, CA, USA | “For seminal contributions to the modeling, simulation and physics of silicon devices.” |
| 2006 – CHANG-GYU HWANG
President and CEO of
Samsung Electronics Co, Ltd
Gyeonggi-Do, Korea | “For contributions to the development of advanced memory products.” |
| 2005 – TSO-PING MA
Raymond John Wean Professor and Chairman of Electrical Engineering
Yale University, New Haven, CT, USA | “For contributions to the development and understanding of CMOS gate dielectrics.” |
| 2004 – KRISHNA SARASWAT
Professor, Dept of Electrical Engrg
Stanford University,
Stanford, CA, USA | “For seminal contributions to silicon process technology.” |
| 2003 – MARK BOHR
Fellow, Director of Process Architecture & Integration
Intel Corporation,
Hillsboro, OR, USA | "For leadership in scaling of advanced CMOS technology for microprocessors." |

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| 2002 – DIMITRI A. ANTONIADIS
Massachusetts Institute of
Technology
Cambridge, MA, USA | "For seminal contributions to field-effect devices and silicon process modeling." |
| 2001 – AL F. TASCH, JR.
University of Texas at Austin,
Austin, TX, USA | "For contributions to MOS technology, and ion implantation and device modeling." |

**Beginning with the year 2001,
the Jack A. Morton Award was renamed the [IEEE Andrew S. Grove Award](#)**

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| 2000 – WOLFGANG FICHTNER
Swiss Federal Institute of
Technology
Zurich, Switzerland | "For outstanding contributions to semiconductor device simulations." |
| 1999 – CHARLES H. HENRY
Lucent Technologies, Bell
Laboratories
Murray Hill, NJ | "For fundamental contributions to the understanding of the optical properties of quantum wells and semiconductor lasers." |
| 1998 – ISAMU AKASAKI
Meijo University
Nagoya, Japan | "For contributions in the field of group-III nitride materials and devices." |
| AND
SHUJI NAKAMURA
Nichia Chemical Industries, Ltd.
Tokushima, Japan | |
| 1997 – CHENMING HU
University of California
Berkeley, CA, USA | "For outstanding contributions to the physics and modeling of MOS device reliability." |
| 1996 – ROBERT W. DUTTON
Stanford University
Stanford, CA, USA | "For seminal contributions to semiconductor process and device modeling." |
| 1995 – YOSHIO NISHI
Hewlett-Packard Company
Palo Alto, CA, USA | "For contributions to the basic understanding and innovative development of MOS device technology." |
| 1994 – ROBERT E. KERWIN
AT&T
Warren, NJ, USA | "For pioneering work and the basic patent on the self-aligned silicon-gate process, a key element in fabrication of very large scale integrated circuits." |
| AND | |

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DONALD L. KLEIN
IBM Corporation
Hopewell Junction, NY, USA

AND

JOHN C. SARACE
Rockwell International
Anaheim, CA, USA

1993 – TOSHIHISA TSUKADA
Hitachi, Ltd.
Tokyo, Japan

"For contributions to the discovery and development of Buried Heterostructure (BH) semiconductor lasers."

1992 – TAKUO SUGANO
University of Tokyo
Tokyo, Japan

"For contributions to Metal-Insulator-Semiconductor Devices and Technology."

1991 – TAK H. NING
HWA N. YU
IBM Corporation
Yorktown Height, NY, USA

"For contributions to the development of advanced bipolar and MOS devices."

1990 – GREGORY E. STILLMAN
University of Illinois
Urbana, IL
and CHARLES M. WOLFE
Washington University
St. Louis, MO, USA

"For the growth and characterization of ultra-high purity gallium arsenide and related compounds."

1989 – CHIH-TANG SAH
University of Illinois
Urbana, IL, USA

"For contributions to the understanding of semiconductor defects and the physics of MOS devices."

1988 – FRANK STERN
IBM Corp.
Yorktown Heights, NY, USA

"For contributions to the theory of injection lasers and two-dimensional electron gases."

1987 – DENNIS D. BUSS
AND
RICHARD A. CHAPMAN
AND
MICHAEL A. KINCH
Texas Instruments
Dallas, TX, USA

"For the demonstration and development of mercury cadmium telluride monolithically- integrated charge-coupled device focal plane arrays."

1986 – HERBERT KROEMER
University of California
Santa Barbara, CA, USA

"For pioneering the theory and device applications of semiconductor heterostructures."

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- 1985 – ROBERT D. BURNHAM
AND
WILLIAM STREIFER
Xerox Corp.
Palo Alto, CA, USA
AND
DONALD R. SCIFRES
Spectra Diode Laboratories
San Jose, CA, USA
"For contributions to electrically pumped distributed feedback lasers and high-power phased-locked laser arrays."
- 1984 – HANS S. RUPPRECHT
AND
JERRY M. WOODALL
IBM Corp.
Yorktown Heights, NY, USA
"For pioneering work in gallium aluminum arsenide heterojunctions and high efficiency light emitting diodes and injection lasers prepared by liquid phase epitaxy."
- 1983 – JUN-ICHI NISHIZAWA
Tohoku University
Sendai, Japan
"For invention and development of the class of static induction transistors (SIT) and for advances in optoelectronic devices."
- 1982 – DOV FROHMAN-BENTCHKOWSKY
INTEL Elec.
Jerusalem, Israel
"For contributions to non-volatile semiconductor memories."
- 1981 – NICK HOLONYAK, JR.
University of Illinois
Urbana, IL, USA
"For pioneering work in quantum well lasers and contributions to visible semiconductor lasers and light-emitting diodes."
- 1980 – JAMES F. GIBBONS
Stanford University
Stanford, CA, USA
"For pioneering contributions to the use of ion implantation in the fabrication of semiconductor devices."
- 1979 – MARTIN P. LEPELTER
Bell Laboratories
Murray Hill, NJ, USA
"For invention of the beam-lead structure and metallurgy used in silicon integrated circuits."
- 1978 – JURI MATISOO
IBM Corp.
Yorktown Heights, NY, USA
"For pioneering the Josephson computer technology."
- 1977 – MORGAN SPARKS
Sandia Corp.
Albuquerque, NM, USA
"For contributions to solid-state device technology and the management of research and development."
- 1976 – ROBERT N. HALL
General Electric Co.
"For outstanding achievement in solid-state physics and chemistry and the

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Schenectady, NY USA

invention and development of
semiconductor devices."